

# isc N-Channel MOSFET Transistor

## IXTA6N50P

### • FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on) ≤ 1.1Ω@V<sub>GS</sub>=10V
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATION



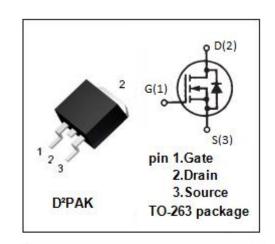
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

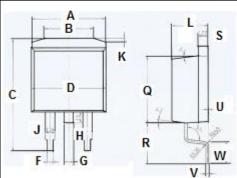
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	500	V
V <sub>GS</sub>	Gate-Source Voltage	±30	V
ID	Drain Current-Continuous	6	А
I <sub>DM</sub>	Drain Current-Single Pulsed	15	А
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25°C	100	W
Tj	Operating Junction Temperature	-55~150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	1.25	°C/W





	mm	
DIM	MIN	MAX
Α	10	
В	6.6	6.8
С	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28 1.6
Н	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
0	8.69	8.71
R	5.28	5.30
R	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 250 μ A	500		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID = 50 μ A	3.0	5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 3A		1.1	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V		±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		5	- μΑ
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 125°C		50	
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> = 6A; V <sub>GS</sub> = 0V		1.5	V



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